**Product data sheet** 

## 1. General description

Ultrafast power diode in a SOD59 (2-lead TO-220AC) plastic package.

### 2. Features and benefits

- · Fast switching
- Guaranteed ESD capability
- High thermal cycling performance
- Low on-state loss
- Low thermal resistance
- Rugged: reverse voltage surge capability
- Soft recovery minimizes power-consuming oscillations

# 3. Applications

Output rectifiers in high-frequency switched-mode power supplies

### 4. Quick reference data

Table 1. Quick reference data

| Symbol                  | Parameter                       | Conditions   |  | Min | Тур | Max   | Unit |
|-------------------------|---------------------------------|--|--|-----|-----|-------|------|
| V <sub>RRM</sub>        | repetitive peak reverse voltage |  |  | -   | -   | 100   | V    |
| I <sub>F(AV)</sub>      | average forward current         | $\delta$ = 0.5 ; T <sub>mb</sub> ≤ 128 °C; square-wave pulse; Fig. 1; Fig. 2   |  | -   | -   | 8     | Α    |
| Static characte         | eristics                        |  |  |     |     |       | ,    |
| V <sub>F</sub>          | forward voltage                 | I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>   |  | -   | 0.8 | 0.895 | V    |
| Dynamic chara           | acteristics                     |  |  |     |     |       |      |
| t <sub>rr</sub>         | reverse recovery time           | $I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; ramp recovery; Fig. 5; Fig. 7 |  | -   | 20  | 25    | ns   |
| Electrostatic discharge |                                 |  |  |     |     |       |      |
| V <sub>ESD</sub>        | electrostatic discharge voltage | HBM; C = 250 pF; R = 1.5 kΩ  |  | -   | -   | 8     | kV   |





Ultrafast power diode

# 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description            | Simplified outline | Graphic symbol |
|-----|--------|------------------------|--------------------|----------------|
| 1   | K      | cathode                | mb                 | K — A          |
| 2   | Α      | anode                  | $rac{1}{2}$        | 001aaa020      |
| mb  | mb     | mounting base; cathode | TO-220AC (SOD59)   |                |

# 6. Ordering information

Table 3. Ordering information

| Type number | Package  |  |         |
|-------------|----------|--|---------|
|             | Name     | Description  | Version |
| BYW29E-100  | TO-220AC | plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC | SOD59   |

# 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol             | Parameter                           | Conditions  | ı | Min | Max | Unit |
|--------------------|-------------------------------------|---|---|-----|-----|------|
| $V_{RRM}$          | repetitive peak reverse voltage     |   |   | -   | 100 | V    |
| $V_{RWM}$          | crest working reverse voltage       |   |   | -   | 100 | V    |
| V <sub>R</sub>     | reverse voltage                     |   |   | -   | 100 | V    |
| I <sub>F(AV)</sub> | average forward current             | $\bar{o}$ = 0.5 ; T <sub>mb</sub> ≤ 128 °C; square-wave pulse; Fig. 1; Fig. 2 |   | -   | 8   | А    |
| I <sub>FRM</sub>   | repetitive peak forward current     | $\delta$ = 0.5 ; $t_p$ = 25 $\mu$ s; $T_{mb} \le$ 128 °C; square-wave pulse   |   | -   | 16  | А    |
| I <sub>FSM</sub>   | non-repetitive peak forward current | $t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse                        |   | -   | 88  | А    |
|                    |                                     | $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse                         |   | -   | 80  | А    |
| I <sub>RRM</sub>   | repetitive peak reverse current     | $\delta = 0.001 \; ; t_p = 2 \; \mu s$  |   | -   | 0.2 | А    |

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| Symbol                  | Parameter                           | Conditions                  |  | Min | Max | Unit |
|-------------------------|-------------------------------------|-----------------------------|--|-----|-----|------|
| I <sub>RSM</sub>        | non-repetitive peak reverse current | t <sub>p</sub> = 100 μs     |  | -   | 0.2 | Α    |
| T <sub>stg</sub>        | storage temperature                 |                             |  | -40 | 150 | °C   |
| Tj                      | junction temperature                |                             |  | -   | 150 | °C   |
| Electrostatic discharge |                                     |                             |  |     |     |      |
| V <sub>ESD</sub>        | electrostatic discharge voltage     | HBM; C = 250 pF; R = 1.5 kΩ |  | -   | 8   | kV   |

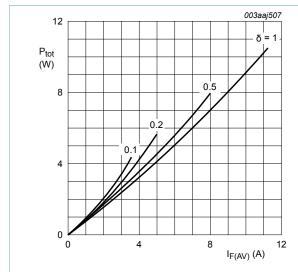


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_{O} &= 0.791 \text{ V}; R_{S} = 0.013 \text{ } \Omega \end{split}$$

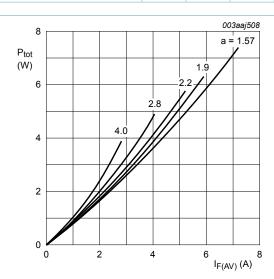


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

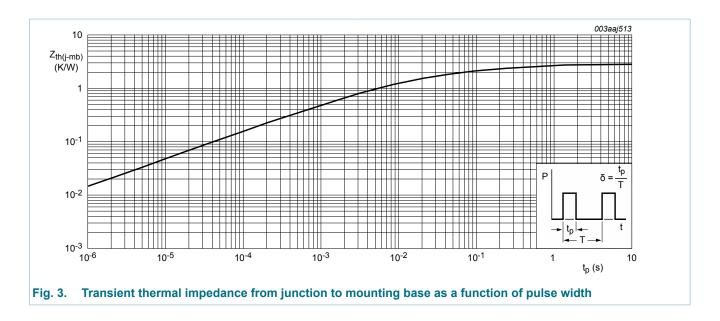
$$\begin{aligned} \mathbf{a} &= \mathbf{form} \ \mathbf{factor} = I_{F(RMS)} / I_{F(AV)} \\ \mathbf{V_O} &= 0.791 \ \mathbf{V}; \ \mathbf{R_S} = 0.013 \ \Omega \end{aligned}$$

## 8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol                | Parameter   | Conditions  | Min | Тур | Max | Unit |
|-----------------------|---|-------------|-----|-----|-----|------|
| R <sub>th(j-mb)</sub> | thermal resistance<br>from junction to<br>mounting base | Fig. 3      | -   | -   | 2.7 | K/W  |
| R <sub>th(j-a)</sub>  | thermal resistance<br>from junction to<br>ambient       | in free air | -   | 60  | -   | K/W  |

### Ultrafast power diode



## 9. Characteristics

Table 6. Characteristics

| Symbol                                | Parameter                | Conditions  | Min | Тур  | Max   | Unit |
|---------------------------------------|--------------------------|---|-----|------|-------|------|
| Static char                           | acteristics              |   |     |      |       |      |
| $V_{F}$                               | forward voltage          | I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 4</u>   | -   | 0.92 | 1.05  | V    |
|                                       |                          | I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 4</u>  | -   | 1.1  | 1.3   | V    |
|                                       |                          | I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>  | -   | 0.8  | 0.895 | V    |
| I <sub>R</sub> reve                   | reverse current          | V <sub>R</sub> = 100 V; T <sub>j</sub> = 25 °C  | -   | 2    | 10    | μA   |
|                                       |                          | V <sub>R</sub> = 100 V; T <sub>j</sub> = 100 °C   | -   | 0.2  | 0.6   | mA   |
| Dynamic cl                            | haracteristics           |   |     |      |       |      |
| Q <sub>r</sub>                        | recovered charge         | $I_F = 2 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 20 \text{ A/}\mu\text{s};$<br>$T_j = 25 \text{ °C}; Fig. 5; Fig. 6$ | -   | 4    | 11    | nC   |
| t <sub>rr</sub> reverse recovery time | reverse recovery time    | $I_F$ = 1 A; $V_R$ = 30 V; $dI_F/dt$ = 100 A/µs;<br>$T_j$ = 25 °C; ramp recovery; <u>Fig. 5</u> ; <u>Fig. 7</u>       | -   | 20   | 25    | ns   |
|                                       |                          | $I_F$ = 0.5 A; $I_R$ = 1 A; $I_{R(meas)}$ = 0.25 A;<br>$T_j$ = 25 °C; step recovery; Fig. 8                           | -   | 15   | 20    | ns   |
| $V_{FRM}$                             | forward recovery voltage | $I_F = 1 \text{ A}; dI_F/dt = 10 \text{ A/}\mu\text{s}; T_j = 25 °C;$<br>Fig. 9                                       | -   | 1    | -     | V    |

#### **Ultrafast power diode**

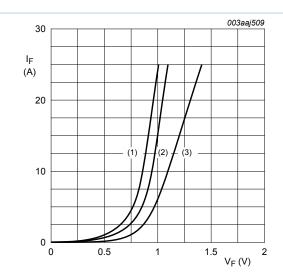


Fig. 4. Forward current as a function of forward voltage

(1)  $T_i = 150$  °C; typical values;

(2) T<sub>i</sub> = 150 °C; maximum values;

(3)  $T_i = 25$  °C; maximum values;

 $V_O = 0.791 \text{ V}; R_S = 0.013 \Omega$ 

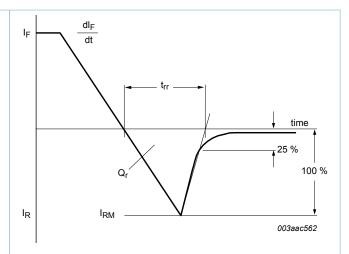


Fig. 5. Reverse recovery definitions; ramp recovery

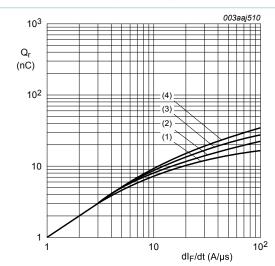


Fig. 6. Recovered charge as a function of rate of change of forward current; maximum values

(1) 
$$I_F = 1 A$$
;  $T_i = 25 \, ^{\circ}\text{C}$ 

(2) 
$$I_F = 2 A$$
;  $T_j = 25 \text{ °C}$ 

(3) 
$$I_F = 5 A$$
;  $T_j = 25 \text{ °C}$ 

(4)  $I_F = 10 A; T_i = 25 °C$ 

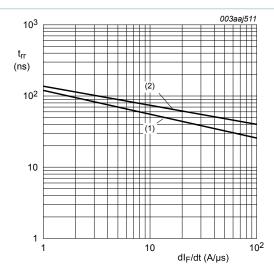
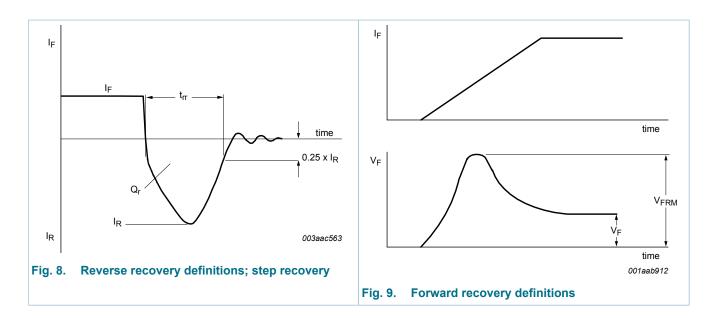


Fig. 7. Reverse recovery time as a function of rate of change of forward current; maximum values

(1) 
$$I_F = 1 A$$
;  $T_i = 25 \, ^{\circ}C$ 

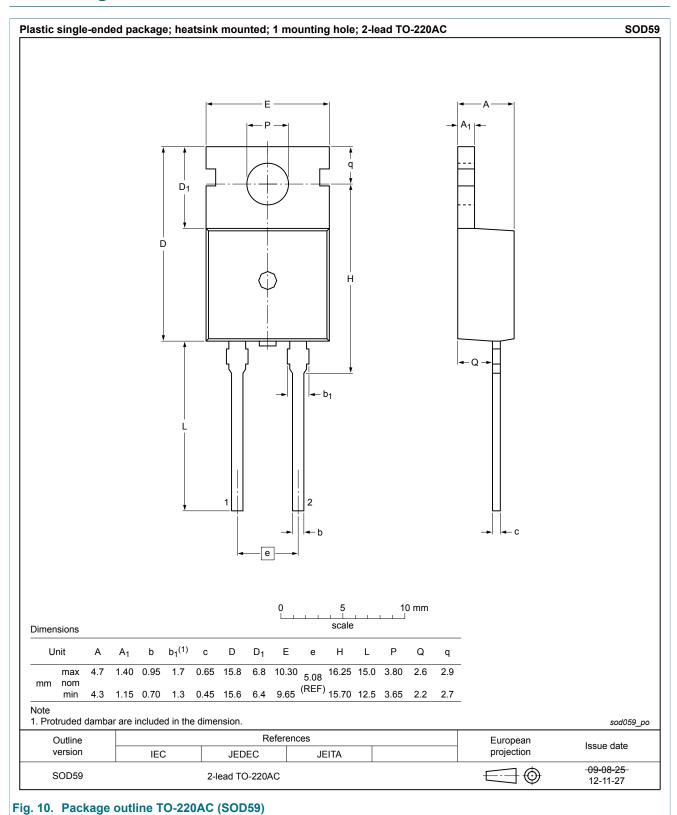
(2) 
$$I_F = 10 \text{ A}; T_j = 25 \text{ }^{\circ}\text{C}$$

### Ultrafast power diode



**Ultrafast power diode** 

## 10. Package outline



#### Ultrafast power diode

## 11. Legal information

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| Document status [1][2]               | Product status [3] | Definition  |
|--------------------------------------|--------------------|---|
| Objective<br>[short] data<br>sheet   | Development        | This document contains data from the objective specification for product development. |
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